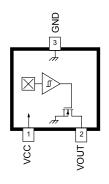
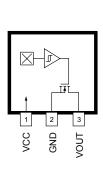
Chopper-Stabilized Hall-Effect Bipolar Switch

Package LH, 3-pin Surface Mount





Package UA, 3-pin SIP





ABSOLUTE MAXIMUM RATINGS

	Supply Voltage, V _{CC}	28 V
	Reverse-Supply Voltage, V _{RCC}	
	Output Off Voltage, V _{OUT}	26.5 V
	Output Current, I _{OUTSINK}	Internally Limited
	Reverse-Output Current, I _{ROUT} .	10 mA
	Magnetic Flux Density, B	Unlimited
	Operating Temperature	
	Ambient, T _A , Range E	40°C to 85°C
	Ambient, T _A , Range L	40°C to 150°C
	Maximum Junction, T _{J(MAX)}	165°C
	Storage Temperature, T _S	
1		

The A3230 Hall-effect sensor is a temperature stable, stress-resistant bipolar switch. This sensor is the most sensitive Hall-effect device in the Allegro® bipolar switch family and is intended for ring-magnet sensing. Superior high-temperature performance is made possible through an Allegro patented dynamic offset cancellation that utilizes chopper-stabilization. This method reduces the offset voltage normally caused by device overmolding, temperature dependencies, and thermal stress.

The A3230 includes the following on a single silicon chip: a voltage regulator, Hall-voltage generator, small-signal amplifier, chopper stabilization, Schmitt trigger, and a short circuit protected open-drain output. Advanced BiCMOS wafer fabrication processing takes advantage of low-voltage requirements, component matching, very low input-offset errors, and small component geometries.

The A3230 Hall-effect bipolar switch turns on in a south polarity magnetic field of sufficient strength and switches off in a north polarity magnetic field of sufficient strength. Because the output state is not defined if the magnetic field is diminished or removed, to ensure that the device switches, Allegro recommends using magnets of both polarities and of sufficient strength in the application.

The A3230 is rated for operation between the ambient temperatures –40°C and 85°C for the E temperature range, and –40°C to 150°C for the L temperature range. Two A3230 package styles provide magnetically optimized solutions for most applications. Package LH is a SOT23W, a miniature low-profile surface-mount package, while package UA is a three-lead ultramini SIP for through-hole mounting. Each package is available in a lead (Pb) free version, with 100% matter tin plated leadframes.

Features and Benefits

- Chopper stabilization
 - · Superior temperature stability
- · Extremely low switchpoint drift
- · Insensitive to physical stress
- Reverse battery protection

- Output short circuit protection
- Solid state reliability
- Small size
- Robust EMC capability
- High ESD ratings (HBM)



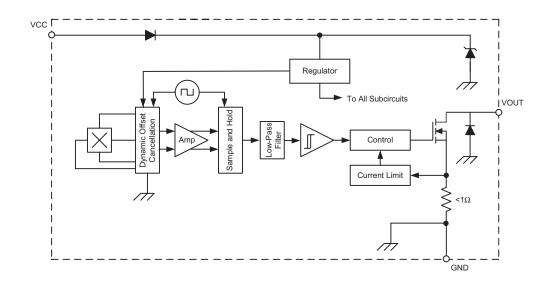


Product Selection Guide

Part Number	Pb- free	Packing*	Mounting	Ambient, T _A (°C)	B _{RP(MIN)} (G)	B _{OP(MAX)} (G)
A3230ELHLT	_	7 in root 2000 pigggg/root	2 nin SOT22W surface mount	-40 to 85		
A3230ELHLT-T	Yes	7-in. reel, 3000 pieces/reel	3-pin SOT23W surface mount			
A3230EUA	_	Bulk, 500 pieces/bag	3 pin SID through holo	-40 10 65		
A3230EUA-T	Yes	Bulk, 500 pieces/bag 3-pin SIP through hole		-25	25	
A3230LLHLT	_	7-in. reel, 3000 pieces/reel	3-pin SOT23W surface mount		-25	25
A3230LLHLT-T	Yes	7-III. Teel, 3000 pieces/feel	3-pin 30123W surface mount	_40 to 150		
A3230LUA	_	Pulk 500 piocos/bag	2 nin SID through halo	_40 to 150		
A3230LUA-T	Yes	Bulk, 500 pieces/bag	3-pin SIP through hole			

^{*}Contact Allegro for additional packing options.

Functional Block Diagram



Terminal List

Nome	Description	Number		
Name	Description	Package LH Package UA		
VCC	Connects power supply to chip	1	1	
VOUT	Output from circuit	2	3	
GND	Ground	3	2	



Chopper-Stabilized Hall Effect Bipolar Switch

OPERATING CHARACTERISTICS valid over full operating voltage and ambient temperature ranges, unless otherwise noted

Characteristic	Symbol	Test Conditions	Min.	Тур.	Max.	Units
Electrical Characteristics			'			
Supply Voltage ¹	V _{CC}	Operating, T _J < 165°C	3.6	_	24	V
Output Leakage Current	I _{OUTOFF}	V _{OUT} = 24 V, B < B _{RP}	-	_	10	μA
Output On Voltage	V _{OUT(SAT)}	I _{OUT} = 20 mA, B > B _{OP}	_	250	500	mV
Output Current Limit	I _{OM}	B > B _{OP}	30	_	60	mA
Power-On Time	t _{PO}	V _{CC} > 3.6 V	-	8	50	μs
Chopping Frequency	f _c		-	200	_	kHz
Output Rise Time ²	t _r	$R_{LOAD} = 820 \Omega, C_S = 20 pF$	_	0.2	1	μs
Output Fall Time ²	t _f	$R_{LOAD} = 820 \Omega, C_S = 20 pF$	_	0.2	1	μs
Supply Current	I _{CCON}	B > B _{OP}	-	1.6	5	mA
Supply Current	I _{CCOFF}	B < B _{RP}	_	1.6	5	mA
Reverse Battery Current	I _{RCC}	V _{RCC} = -18 V	-	_	-2	mA
Supply Zener Clamp Voltage	V _Z	I _{CC} = 8 mA; T _A = 25°C	28	-	_	V
Supply Zener Current ³	I _Z	V _S = 28 V	_	_	8	mA
Magnetic Characteristics ⁴			-			•
Operate Point	B _{OP}	South pole adjacent to branded face of device	-10	7.5	25	G
Release Point	B _{RP}	North pole adjacent to branded face of device	-25	-7.5	10	G
Hysteresis	B _{HYS}	B _{OP} – B _{RP}	5	15	25	G

¹ Maximum voltage must be adjusted for power dissipation and junction temperature, see *Power Derating* section.

DEVICE QUALIFICATION PROGRAM

Contact Allegro for information.

EMC (Electromagnetic Compatibility) REQUIREMENTS Contact Allegro for information.



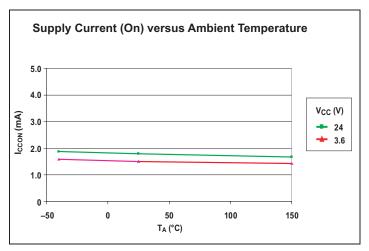
 $^{^{2}}$ C_S = oscilloscope probe capacitance.

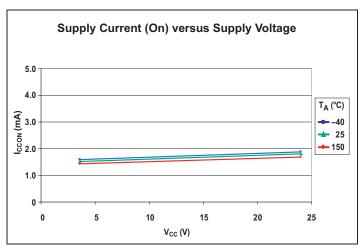
 $^{^3}$ Maximum current limit is equal to the maximum $I_{\text{CC}(\text{MAX})}$ + 3 mA.

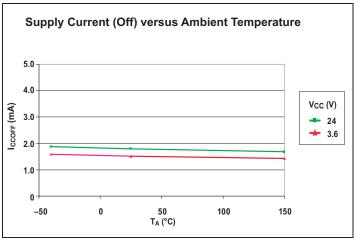
⁴ Magnetic flux density, B, is indicated as a negative value for north-polarity magnetic fields, and as a positive value for south-polarity magnetic fields. This so-called algebraic convention supports arithmetic comparison of north and south polarity values, where the relative strength of the field is indicated by the absolute value of B, and the sign indicates the polarity of the field (for example, a -100 G field and a 100 G field have equivalent strength, but opposite polarity).

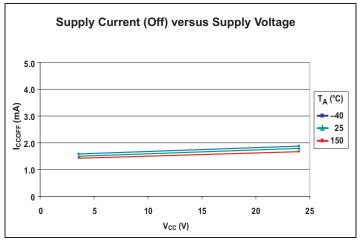
Chopper-Stabilized Hall Effect Bipolar Switch

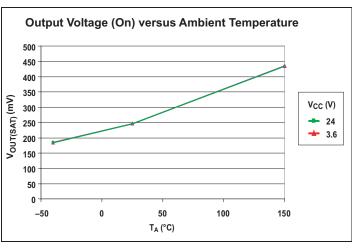
Electrical Characteristic Data

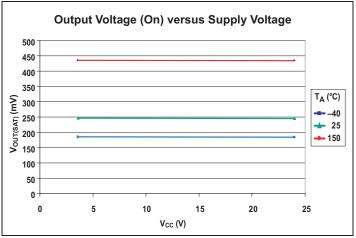






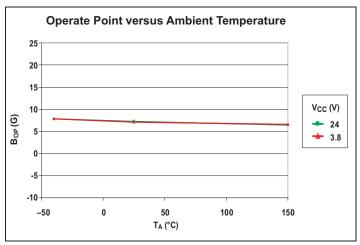


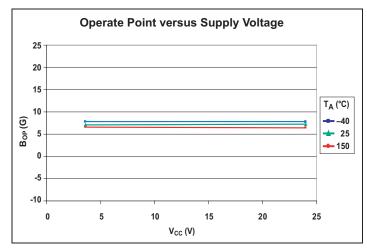


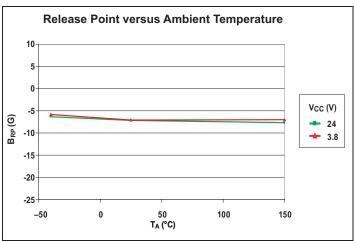


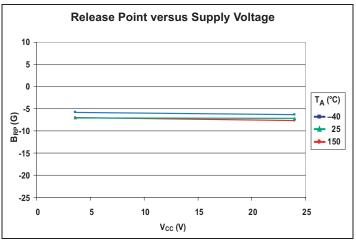
Chopper-Stabilized Hall Effect Bipolar Switch

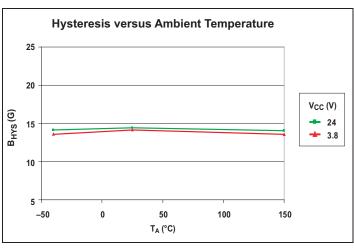
Magnetic Characteristic Data

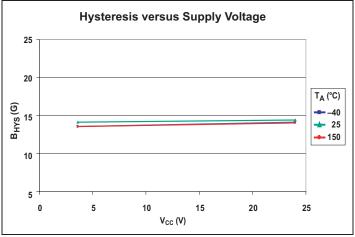












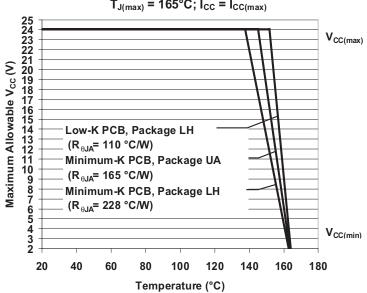
Chopper-Stabilized Hall Effect Bipolar Switch

THERMAL CHARACTERISTICS may require derating at maximum conditions, see application information

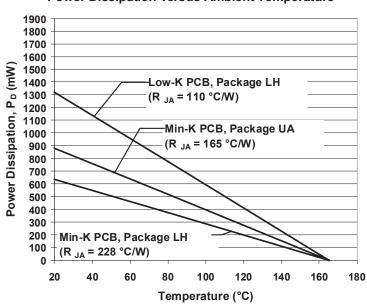
Characteristic	Symbol	Test Conditions	Value	Units
Package Thermal Resistance	$R_{ heta JA}$	Package LH, minimum-K PCB (single-sided with copper limited to solder pads)	110	°C/W
		Package LH, low-K PCB (double-sided with 0.926 in ² copper area)	228	°C/W
		Package UA, minimum-K PCB (single-sided with copper limited to solder pads)	165	°C/W

Power Derating Curve





Power Dissipation versus Ambient Temperature





Chopper-Stabilized Hall Effect Bipolar Switch

Functional Description

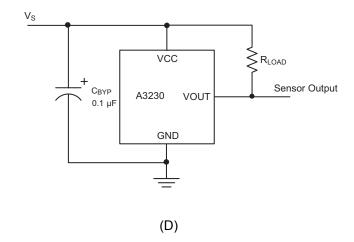
Operation

The output of these devices switches low (turns on) when a magnetic field perpendicular to the Hall sensor exceeds the operate point threshold, BOP. After turn-on, the output voltage is V_{OUT(SAT)}. The output transistor is capable of sinking current up to the short circuit current limit, I_{OM}, which is a minimum of 30 mA. When the magnetic field is reduced below the release point, B_{RP}, the device output goes high (turns off). The difference in the magnetic operate and release points is the hysteresis, B_{HYS}, of the device. This built-in hysteresis allows clean switching of the output even in the presence of external mechanical vibration and electrical noise.

There are three switching modes for bipolar devices, referred to as latch, unipolar switch, and negative switch. Mode is determined by the switchpoint characteristics of the individual device. Note that, as shown in figure 1, these switchpoints can lie in either north or south polarity ranges. The values of the magnetic parameters for the A3230 are specified in the Magnetic Characteristics table, on page 3.

Bipolar devices typically behave as latches (although these devices are not guaranteed to do so). In this mode, magnetic fields of opposite polarity and equivalent strengths are needed to switch the output. When the magnetic fields are removed $(B \rightarrow 0)$ the device remains in the same state until a magnetic field of the opposite polarity and of sufficient strength causes it to switch. The hysteresis of latch mode behavior is shown in panel A of figure 1.

In contrast to latching, when a device exhibits unipolar switching, it only responds to a south magnetic field. The field must be of sufficient strength, $> B_{OP}$, for the device to operate. When the field is reduced beyond the B_{RP} level, the device switches back to the high state, as shown in panel B of figure 1. Devices



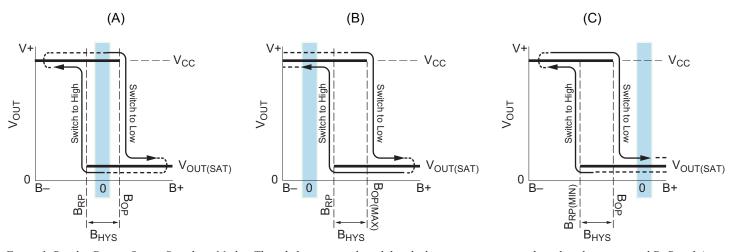


Figure 1. Bipolar Device Output Switching Modes. These behaviors can be exhibited when using a circuit such as that shown in panel D. Panel A displays the hysteresis when a device exhibits latch mode (note that the B_{HYS} band incorporates B=0), panel B shows unipolar switch behavior (the B_{HYS} band is more positive than B=0), and panel C shows negative switch behavior (the B_{HYS} band is more negative than B=0). Bipolar devices, such as the A3230, can operate in any of the three modes.



Chopper-Stabilized Hall Effect Bipolar Switch

exhibiting negative switch behavior operate in a similar but opposite manner. A north polarity field of sufficient strength, > B_{RP} , (more north than B_{RP}) is required for operation, although the result is that V_{OUT} switches high, as shown in panel C. When the field is reduced beyond the B_{OP} level, the device switches back to the low state.

The A3230 is designed to attain a small hysteresis, and thereby provide more sensitive switching. Although this means that true latching behavior cannot be guaranteed in all cases, proper switching can be ensured by use of both south and north magnetic fields, as in a ring magnet.

Bipolar devices adopt an indeterminate output state when powered-on in the absence of a magnetic field or in a field that lies within the hysteresis band of the device. The correct state is attained after the first excursion beyond B_{OP} or B_{RP}.

For more information on Bipolar switches, refer to Application Note 27705, Understanding Bipolar Hall Effect Sensors.

Applications

It is strongly recommended that an external bypass capacitor be connected (in close proximity to the Hall sensor) between the supply and ground of the device to reduce both external noise and noise generated by the chopper stabilization technique. As is shown in Panel B of figure 1, a 0.1µF capacitor is typical.

Extensive applications information on magnets and Hall-effect sensors is available in:

- Hall-Effect IC Applications Guide, AN27701,
- Hall-Effect Devices: Gluing, Potting, Encapsulating, Lead Welding and Lead Forming, AN27703.1
- Soldering Methods for Allegro's Products SMT and Through-Hole, AN26009

All are provided in Allegro Electronic Data Book, AMS-702 and the Allegro Web site: www.allegromicro.com



Chopper-Stabilized Hall Effect Bipolar Switch

Chopper Stabilization Technique

When using Hall-effect technology, a limiting factor for switchpoint accuracy is the small signal voltage developed across the Hall element. This voltage is disproportionally small relative to the offset that can be produced at the output of the Hall sensor. This makes it difficult to process the signal while maintaining an accurate, reliable output over the specified operating temperature and voltage ranges.

Chopper stabilization is a unique approach used to minimize Hall offset on the chip. The patented Allegro technique, namely Dynamic Quadrature Offset Cancellation, removes key sources of the output drift induced by thermal and mechanical stresses. This offset reduction technique is based on a signal modulationdemodulation process. The undesired offset signal is separated from the magnetic-field-induced signal in the frequency domain, through modulation. The subsequent demodulation acts as a modulation process for the offset, causing the magnetic-fieldinduced signal to recover its original spectrum at baseband, while the dc offset becomes a high-frequency signal. The magnetic-field-induced signal then can pass through a low-pass filter, while the modulated dc offset is suppressed. This configuration is illustrated in figure 2.

The chopper stabilization technique uses a 200 kHz high-frequency clock. For demodulation process, a sample and hold technique is used, where the sampling is performed at twice the chopper frequency (400 kHz). This high-frequency operation allows a greater sampling rate, which results in higher accuracy and faster signal-processing capability. This approach desensitizes the chip to the effects of thermal and mechanical stresses, and produces devices that have extremely stable quiescent Hall output voltages and precise recoverability after temperature cycling. This technique is made possible through the use of a BiCMOS process, which allows the use of low-offset, low-noise amplifiers in combination with high-density logic integration and sample-and-hold circuits.

The repeatability of magnetic-field-induced switching is affected slightly by a chopper technique. However, the Allegro highfrequency chopping approach minimizes the affect of jitter and makes it imperceptible in most applications. Applications that are more likely to be sensitive to such degradation are those requiring precise sensing of alternating magnetic fields; for example, speed sensing of ring-magnet targets. For such applications, Allegro recommends its digital sensor families with lower sensitivity to jitter. For more information on those devices, contact your Allegro sales representative.

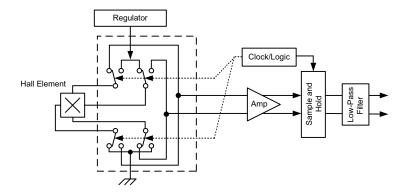


Figure 2. Chopper Stabilization Circuit (Dynamic Quadrature Offset Cancellation)



Chopper-Stabilized Hall Effect Bipolar Switch

Power Derating

The device must be operated below the maximum junction temperature of the device, T_{J(max)}. Under certain combinations of peak conditions, reliable operation may require derating supplied power or improving the heat dissipation properties of the application. This section presents a procedure for correlating factors affecting operating T_I. (Thermal data is also available on the Allegro MicroSystems Web site.)

The Package Thermal Resistance, $R_{\theta JA}$, is a figure of merit summarizing the ability of the application and the device to dissipate heat from the junction (die), through all paths to the ambient air. Its primary component is the Effective Thermal Conductivity, K, of the printed circuit board, including adjacent devices and traces. Radiation from the die through the device case, R_{AIC} , is relatively small component of $R_{\theta JA}$. Ambient air temperature, T_A, and air motion are significant external factors, damped by overmolding.

The effect of varying power levels (Power Dissipation, P_D), can be estimated. The following formulas represent the fundamental relationships used to estimate T_J , at P_D .

$$P_D = V_{IN} \times I_{IN} \tag{1}$$

$$\Delta T = P_D \times R_{\theta IA} \tag{2}$$

$$T_{I} = T_{A} + \Delta T \tag{3}$$

For example, given common conditions such as: $T_A = 25$ °C, $V_{CC} = 12 \text{ V}, I_{CC} = 1.5 \text{ mA}, \text{ and } R_{\theta \text{IA}} = 165 \text{ °C/W}, \text{ then:}$

$$P_D = V_{CC} \times I_{CC} = 12 \text{ V} \times 1.5 \text{ mA} = 18 \text{ mW}$$

$$\Delta T = P_D \times R_{\theta IA} = 18 \text{ mW} \times 165 \text{ }^{\circ}\text{C/W} = 3 \text{ }^{\circ}\text{C}$$

$$T_J = T_A + \Delta T = 25^{\circ}C + 3^{\circ}C = 28^{\circ}C$$

A worst-case estimate, $P_{D(max)}$, represents the maximum allowable power level ($V_{CC(max)}$, $I_{CC(max)}$), without exceeding $T_{J(max)}$, at a selected $R_{\theta JA}$ and T_A .

Example: Reliability for V_{CC} at T_A=150°C, package LH, using a low-K PCB.

Observe the worst-case ratings for the device, specifically: $R_{\theta JA} = 228 \text{ °C/W}, T_{J(max)} = 165 \text{ °C}, V_{CC(max)} = 24 \text{ V}, \text{ and}$ $I_{CC(max)} = 5 \text{ mA}.$

Calculate the maximum allowable power level, P_{D(max)}. First, invert equation 3:

$$\Delta T_{\text{max}} = T_{\text{J(max)}} - T_{\text{A}} = 165 \,^{\circ}\text{C} - 150 \,^{\circ}\text{C} = 15 \,^{\circ}\text{C}$$

This provides the allowable increase to T_I resulting from internal power dissipation. Then, invert equation 2:

$$P_{D(max)} = \Delta T_{max} \div R_{\theta JA} = 15^{\circ}C \div 228^{\circ}C/W = 66 \text{ mW}$$

Finally, invert equation 1 with respect to voltage:

$$V_{CC(est)} = P_{D(max)} \div I_{CC(max)} = 66 \text{ mW} \div 5 \text{ mA} = 13 \text{ V}$$

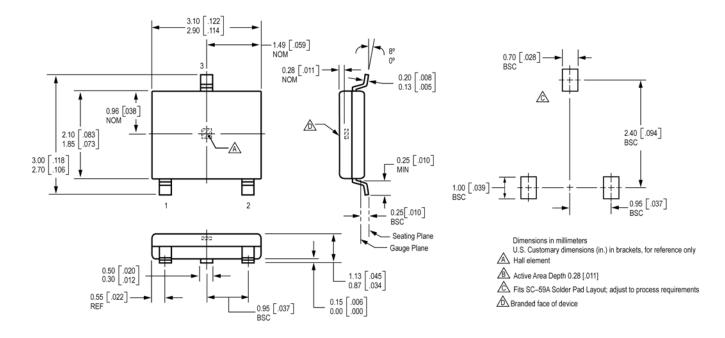
The result indicates that, at T_A, the application and device can dissipate adequate amounts of heat at voltages $\leq V_{CC(est)}$.

Compare $V_{CC(est)}$ to $V_{CC(max)}$. If $V_{CC(est)} \le V_{CC(max)}$, then reliable operation between $V_{CC(est)}$ and $V_{CC(max)}$ requires enhanced $R_{\theta JA}$. If $V_{CC(est)} \ge V_{CC(max)}$, then operation between $V_{CC(est)}$ and $V_{CC(max)}$ is reliable under these conditions.

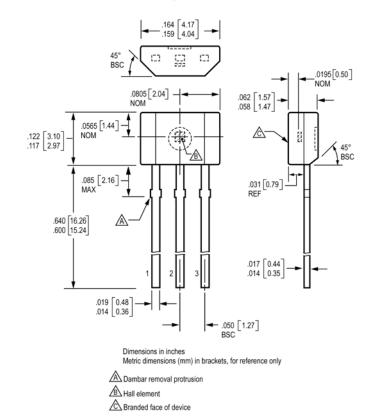


Chopper-Stabilized Hall Effect Bipolar Switch

Package LH, 3-Pin (SOT-23W)



Package UA, 3-Pin





Worcester, Massachusetts 01615-0036 (508) 853-5000

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Chopper-Stabilized Hall Effect Bipolar Switch

The products described herein are manufactured under one or more of the following U.S. patents: 5,045,920; 5,264,783; 5,442,283; 5,389,889; 5,581,179; 5,517,112; 5,619,137; 5,621,319; 5,650,719; 5,686,894; 5,694,038; 5,729,130; 5,917,320; and other patents pending.

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